



PROJECTION SCANNER

## SUSS DSC300 Gen3

PROJECTION LITHOGRAPHY SCANNER FOR WLP, 2.5D & 3D PACKAGING, BUMPING AND FAN-OUT APPLICATIONS

SUSS MicroTec introduces its next generation projection scanner – the DSC300 Gen3. This proprietary scanning lithography platform touts triple digit throughput with fine (2  $\mu\text{m}$ ) resolution capabilities at the lowest cost of ownership (CoO) among 1X projection lithography systems.

Re-engineered with a large diamond shaped scan beam and highly minimized overhead time – the DSC300 Gen3 Scanner delivers 300 mm wafer throughput of >90 wph at 400 mJ/cm<sup>2</sup> and >80 wph at 1000 mJ/cm<sup>2</sup>.

Its enhanced 1X Wynne-Dyson optics and four recipe selectable numerical apertures enable the achievement of fine 2  $\mu\text{m}$  features in thin resist, as well as > 100  $\mu\text{m}$  DoF in thick resist. The DSC300's full-field imaging technology supports industry roadmaps for large die patterning and mixed die packaging in heterogeneous integration without stitching or pattern size limits.

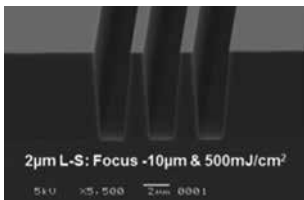
The state-of-the-art vision and alignment system includes both on-axis and off-axis cameras for maximum flexibility and an overlay accuracy of  $\leq 1.0 \mu\text{m}$  (mean + 3  $\sigma$ ). The DSC300 Gen3 is also equipped with proprietary Optical Magnification Correction and Beam Steering Technology which is invaluable in compensating for large amounts of die shift

### HIGHLIGHTS

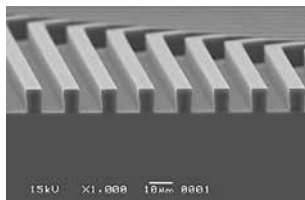
- + > 90 wph for 300 mm wafers at 400 mJ/cm<sup>2</sup> dose
- + Lowest cost of ownership among 1X projection lithography tools
- + 2/2  $\mu\text{m}$  L/S resolution and  $\leq 1.0 \mu\text{m}$  overlay (mean + 3  $\sigma$ )
- + Full-field large-die patterning with no stitching
- + Active optical magnification compensation and beam steering to correct die shift errors in FOWLP



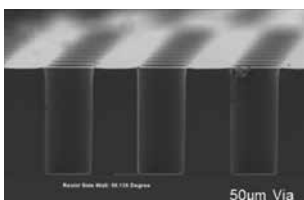
in FOWLP applications, as well as common wafer run-in and run-out. Symmetric magnification to  $\pm 200 \text{ ppm}$  ( $\pm 30 \mu\text{m}$  on a 300 mm wafer) is available without throughput or resolution impact.



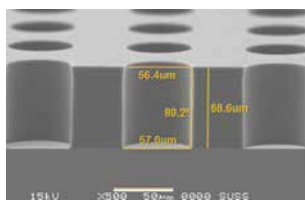
2  $\mu\text{m}$  L/S in 7  $\mu\text{m}$  TOK-PW1000T



10  $\mu\text{m}$  L/S in 12  $\mu\text{m}$  AZ15nxT



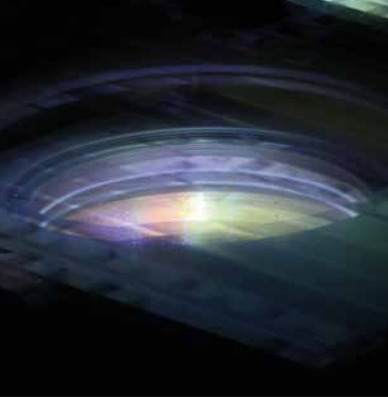
50  $\mu\text{m}$  vias in 115  $\mu\text{m}$  ASAHI-CX-A240



50  $\mu\text{m}$  vias in 63  $\mu\text{m}$  TOK CR-4000

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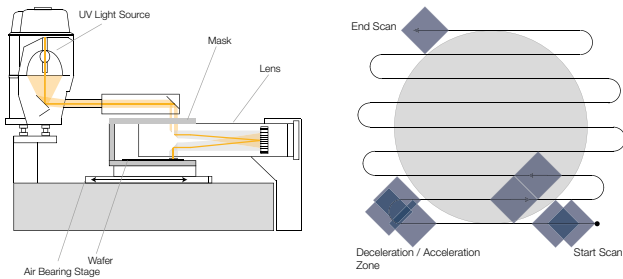
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## TECHNICAL DATA

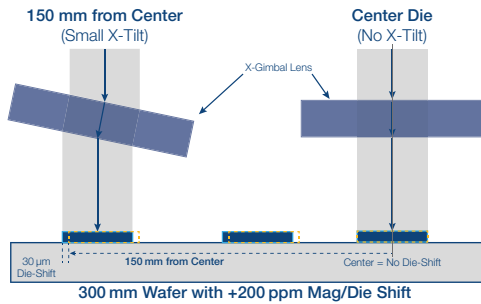
### CORE TECHNOLOGY: *Scanning Projection Lithography*

Mask and wafer are co-mounted on a scanning stage. The system scans in a serpentine pattern with controlled velocity in the x-axis and precision stepping in the y-axis. Excellent exposure uniformity is achieved over the entire exposure area by scanning with a high intensity homogenized beam, overlapping adjacent scans, and precisely controlling the scan velocity.



Continuous serpentine scanning technique with diamond shaped beam

### NEW TECHNOLOGY: *Optical Die Shift Compensation*



X-Gimbal lens angle adjusted in sync with stage position to compensate for mag/die shift

Data, design and specification depend on individual process conditions and can vary according to equipment configurations. Not all specifications may be valid simultaneously. Illustrations, photos and specifications in this brochure are not legally binding. SUSS MicroTec reserves the right to change machine specifications without prior notice.



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### EXPOSURE SYSTEM

<b>Exposure Mode</b>	Full-field projection scanning (Dyson optics)
<b>Resolution</b>	2 µm L/S 2 µm resist
<b>Numerical Aperture</b>	Four selectable: 0.15, 0.14, 0.10, 0.07 NA
<b>Imaging</b>	Non-contact, single-side exposure
<b>Wavelength Selection</b>	350-450 nm selectable
<b>Exposure Uniformity</b>	< ±3%
<b>Environmental Control</b>	ECU (±0.2 °C)

### ALIGNMENT SYSTEM

<b>Top-side Alignment</b>	Optical: On-axis and off-axis IR: Off-axis (optional)
<b>Back-side Alignment</b>	IR TSA (optional)
<b>Overlay Accuracy (Tool to Self)</b>	Optical: ≤ 1.0 µm (mean + 3σ) IR: ≤ 2.5 µm (mean + 3σ)
<b>Run-in/ Run-out Control</b>	Mask cooling (standard) Optional Optical Mag Correction and Beam Steering: Symmetric correction: ± 200 ppm
<b>Fan-Out Die Shift Compensation</b>	Optional Optical Mag Correction and Beam Steering: Symmetric correction: ± 200 ppm

### WAFER AND MASK HANDLING

<b>Wafers</b>	300 mm (optional 200 mm and 330 mm)
<b>Allowable Warpage</b>	< 2 mm (standard); up to 5 mm (customized)
<b>Carrier Mounted Substrates</b>	Yes
<b>Thin Substrates w/o Carrier</b>	Thickness down to 200 µm
<b>Wafer Loading</b>	Fully automated
<b>Mask Loading</b>	Fully automated
<b>Mask</b>	Full field (entire substrate layout)
<b>Mask Sizes</b>	14" (300mm wafers); Optional 9" (200mm wafers)
<b>Pellicle Mask Handling</b>	Optional

### DIMENSIONS

<b>Width x Depth x Height</b>	3220mm x 4197 mm x 2466 mm (incl. peripherals)
<b>Weight</b>	Main tool: 4587 kg; EFEM: 562 kg; ECU: 290 kg

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